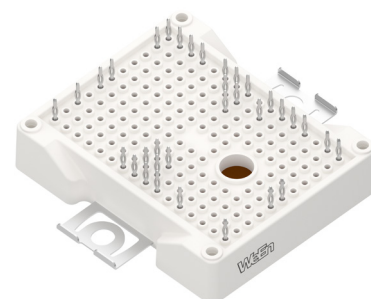


1. General description

WMG100N07B2P-S is a I-type NPC (Neutral Point Clamped) three-level module consisting of two 100A, 650V outer IGBTs with inverse diodes, two 100A, 650V inner IGBTs with inverse diodes, two neutral point 100A, 650 V diodes and an NTC thermistor. The integrated field stop trench IGBTs and FRDs provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability.



2. Features and benefits

- I-NPC topology
- Low switching losses
- Low Vcesat
- Compact design
- Pressfit pin
- Integrated NTC temperature sensor
- Al₂O₃ substrate with low thermal resistance

3. Applications

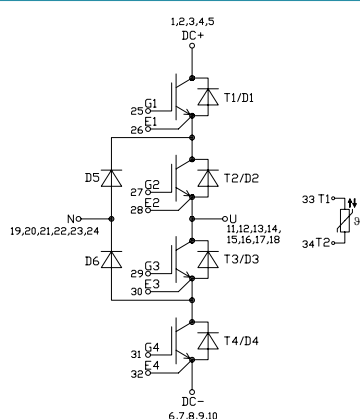
- Three-level applications
- Solar
- Motor Drives
- UPS

4. Ordering information

Table 1. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMG100N07B2P-S	WeEnPACK-B2	WMG100N07B2P-ST	Tray	14	WeEnPACK-B2PTL-F	16-Jul-2024

5. Circuit diagram



6. Limiting values

Table 2. Limiting values

Symbol	Parameter	Test Condition	Value	Unit
IGBT, T1/T2/T3/T4				
V_{CE}	Collector-emitter voltage		650	V
V_{GE}	Gate-emitter voltage		± 20	V
I_{CN}	Implemented collector current		200	A
I_C	Continuous collector current	$T_C = 95\text{ }^{\circ}\text{C}$, limited by T_{jmax}	100	A
I_{Cpulse}	Pulsed collector current	tp limited by T_{jmax}	300	A
P_{tot}	Total power dissipation	$T_C = 95\text{ }^{\circ}\text{C}$	160	W
t_{sc}	Short circuit withstand time	$V_{GE} = 15\text{ V}$; $V_{CC} = 400\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$	5	μs
T_{jmax}	Maximum junction temperature		175	$^{\circ}\text{C}$
Diode, D1/D2/D3/D4/D5/D6				
V_{RRM}	Diode repetitive peak reverse voltage		650	V
I_{FN}	Diode Implemented collector current		200	A
I_F	Diode Continuous collector current	$T_C = 95\text{ }^{\circ}\text{C}$, limited by T_{jmax}	100	A
I_{FRM}	Diode repetitive peak forward current	tp limited by T_{jmax}	300	A
P_{tot}	Total power dissipation	$T_C = 95\text{ }^{\circ}\text{C}$	145	W
T_{jmax}	Maximum junction temperature		175	$^{\circ}\text{C}$

7. Module package thermal & insulation properties

Table 3. Thermal & Insulation properties

Symbol	Parameter	Test Condition	Value	Unit
V_{ISOL}	RMS isolation voltage	$T_j = 25\text{ }^{\circ}\text{C}$, all terminals shorted, $f = 50\text{ Hz}$, $t = 1\text{ min}$	2500	V
d_{Creep}	Creepage distance	terminal to heatsink	11.5	mm
d_{Clear}	Clearance	terminal to heatsink	10	mm
CTI	Comperative tracking index		> 200	
T_{stg}	Storage temperature		-40 to 125	$^{\circ}\text{C}$

8. Electrical characteristics

Table 4. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Outer IGBT characteristics, T1/T4						
V_{CEsat}	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}; I_C = 100\text{ A}; T_J = 25\text{ °C}$	-	1.6	-	V
		$V_{GE} = 15\text{ V}; I_C = 100\text{ A}; T_J = 150\text{ °C}$	-	2.1	-	V
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C = 0.5\text{ mA}; V_{CE} = V_{GE}; T_J = 25\text{ °C}$	3.6	4.8	6.0	V
I_{CES}	Zero gate voltage collector current	$V_{CE} = 650\text{ V}; V_{GE} = 0\text{ V}; T_J = 25\text{ °C}$	-	-	20	μA
I_{GES}	Gate leakage current	$V_{GE} = 20\text{ V}; V_{CE} = 0\text{ V}; T_J = 25\text{ °C}$	-	-	200	nA
Q_G	Gate charge	$V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}$	-	307	-	nC
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}; T_J = 25\text{ °C}$	-	4329	-	pF
C_{oes}	Output capacitance		-	281	-	pF
C_{res}	Reverse transfer capacitance		-	77	-	pF
$t_{d(on)}$	Turn-on delay time	$T_J = 25\text{ °C}$ $V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}; R_g = 10\text{ }\Omega$	-	42	-	nS
t_r	Rise time		-	35	-	nS
$t_{d(off)}$	Turn-off delay time		-	155	-	nS
t_f	Fall time		-	60	-	nS
E_{on}	Turn-on energy		-	1.5	-	mJ
E_{off}	Turn-off energy		-	1.2	-	mJ
$t_{d(on)}$	Turn-on delay time	$T_J = 150\text{ °C}$ $V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}; R_g = 10\text{ }\Omega$	-	38	-	nS
t_r	Rise time		-	40	-	nS
$t_{d(off)}$	Turn-off delay time		-	164	-	nS
t_f	Fall time		-	83	-	nS
E_{on}	Turn-on energy		-	2.4	-	mJ
E_{off}	Turn-off energy		-	1.6	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.5	-	K/W
T_{jop}	Operation temperature		-40		150	$^{\circ}\text{C}$
Neutral point Diode characteristics, D5/D6						
V_F	Diode forward voltage	$I_F = 100\text{ A}; T_J = 25\text{ °C}$	-	1.75	-	V
		$I_F = 100\text{ A}; T_J = 150\text{ °C}$	-	1.5	-	V
Q_{rr}	Reverse recovery charge	$T_J = 25\text{ °C}$ $V_R = 300\text{ V}; I_F = 100\text{ A}; di/dt = 2300\text{ A}/\mu\text{s};$	-	742	-	nC
I_{rrm}	Peak reverse recovery current		-	34	-	A
E_{rr}	Reverse recovery energy		-	0.12	-	mJ
Q_{rr}	Reverse recovery charge	$T_J = 150\text{ °C}$ $V_R = 300\text{ V}; I_F = 100\text{ A}; di/dt = 2300\text{ A}/\mu\text{s};$	-	3141	-	nC
I_{rrm}	Peak reverse recovery current		-	47	-	A
E_{rr}	Reverse recovery energy		-	0.54	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.8	-	K/W
T_{jop}	Operation temperature		-40		150	$^{\circ}\text{C}$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Inner IGBT characteristics, T2/T3						
V_{CEsat}	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}; I_C = 100\text{ A}; T_j = 25\text{ °C}$	-	1.6	-	V
		$V_{GE} = 15\text{ V}; I_C = 100\text{ A}; T_j = 150\text{ °C}$	-	2.1	-	V
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C = 0.5\text{ mA}; V_{CE} = V_{GE}; T_j = 25\text{ °C}$	3.6	4.8	6.0	V
I_{CES}	Zero gate voltage collector current	$V_{CE} = 650\text{ V}; V_{GE} = 0\text{ V}; T_j = 25\text{ °C}$	-	-	20	μA
I_{GES}	Gate leakage current	$V_{GE} = 20\text{ V}; V_{CE} = 0\text{ V}; T_j = 25\text{ °C}$	-	-	200	nA
Q_G	Gate charge	$V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}$	-	307	-	nC
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ °C}$	-	4329	-	pF
C_{oes}	Output capacitance		-	281	-	pF
C_{res}	Reverse transfer capacitance		-	77	-	pF
$t_{d(on)}$	Turn-on delay time	$T_j = 25\text{ °C}$ $V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}; R_g = 10\text{ }\Omega$	-	41	-	nS
t_r	Rise time		-	27	-	nS
$t_{d(off)}$	Turn-off delay time		-	150	-	nS
t_f	Fall time		-	46	-	nS
E_{on}	Turn-on energy		-	1.0	-	mJ
E_{off}	Turn-off energy		-	1.2	-	mJ
$t_{d(on)}$	Turn-on delay time	$T_j = 150\text{ °C}$ $V_{CC} = 300\text{ V}; I_C = 100\text{ A}; V_{GE} = \pm 15\text{ V}; R_g = 10\text{ }\Omega$	-	38	-	nS
t_r	Rise time		-	32	-	nS
$t_{d(off)}$	Turn-off delay time		-	163	-	nS
t_f	Fall time		-	72	-	nS
E_{on}	Turn-on energy		-	1.8	-	mJ
E_{off}	Turn-off energy		-	1.6	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.5	-	K/W
T_{jop}	Operation temperature		-40		150	$^{\circ}\text{C}$
Inverse Diode characteristics, D1/D2/D3/D4						
V_F	Diode forward voltage	$I_F = 100\text{ A}; T_j = 25\text{ °C}$	-	1.75	-	V
		$I_F = 100\text{ A}; T_j = 150\text{ °C}$	-	1.5	-	V
Q_{rr}	Reverse recovery charge	$T_j = 25\text{ °C}$ $V_R = 300\text{ V}; I_F = 100\text{ A}; di/dt = 3000\text{ A}/\mu\text{s};$	-	976	-	nC
I_{rrm}	Peak reverse recovery current		-	47	-	A
E_{rr}	Reverse recovery energy		-	0.2	-	mJ
Q_{rr}	Reverse recovery charge	$T_j = 150\text{ °C}$ $V_R = 300\text{ V}; I_F = 100\text{ A}; di/dt = 3000\text{ A}/\mu\text{s};$	-	3680	-	nC
I_{rrm}	Peak reverse recovery current		-	50	-	A
E_{rr}	Reverse recovery energy		-	0.76	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.8	-	K/W
T_{jop}	Operation temperature		-40		150	$^{\circ}\text{C}$

9. NTC - thermistor

Table 5. NTC - Thermistor

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R ₂₅	Rated resistance	T _c = 25 °C	-	5000	-	Ω
R ₁₀₀		T _c = 100 °C	465±5%			Ω
B _{25/50}	B-value	$R_2=R_{25} \exp.[B_{25/50}(1/T_2-1(298.15K))]$	3380±5%			K

Typical Characteristics - IGBT T1/T2/T3/T4 and Diode D1/D2/D3/D4/D5/D6

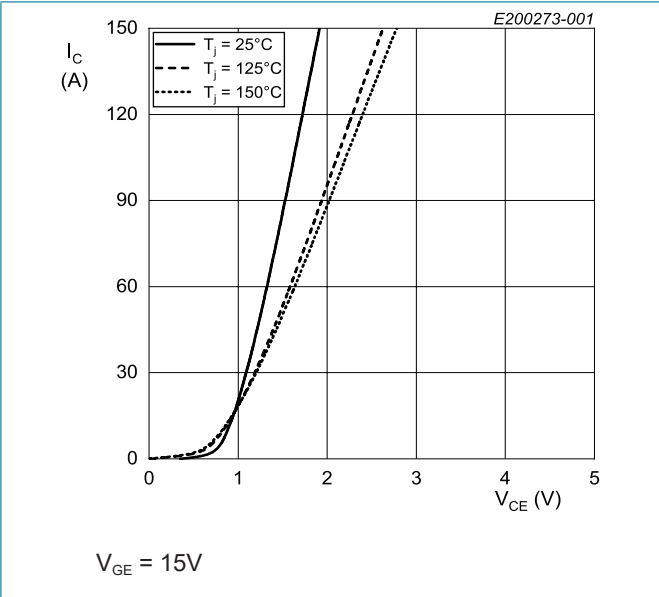


Fig. 1. IGBT typical output characteristics, T1/T2/T3/T4

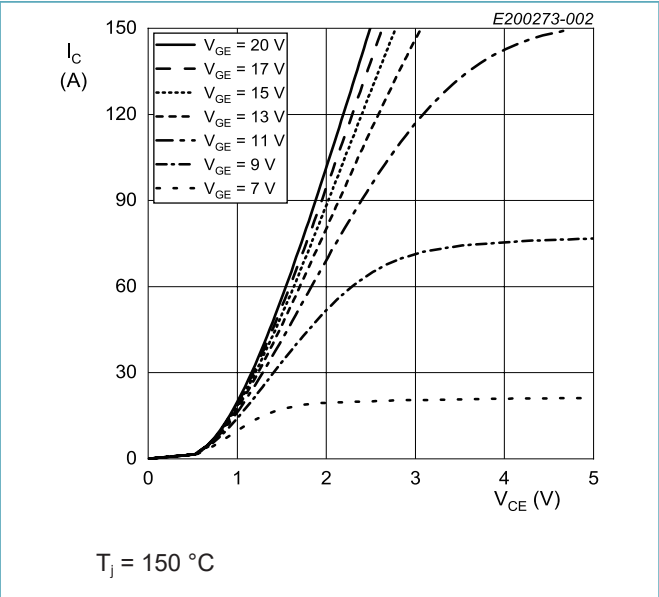


Fig. 2. IGBT typical output characteristics, T1/T2/T3/T4

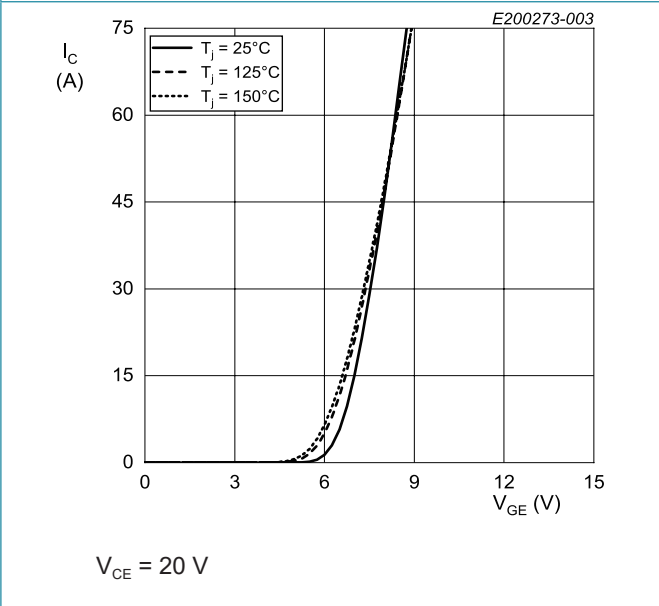


Fig. 3. IGBT typical transfer characteristics, T1/T2/T3/T4

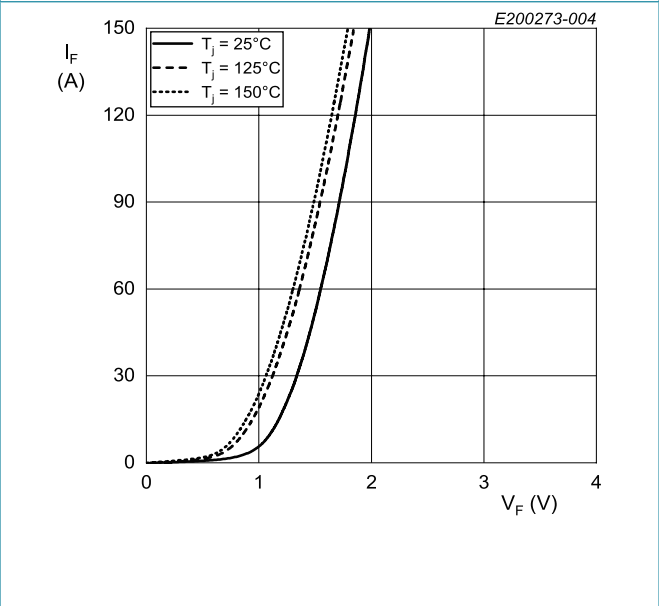
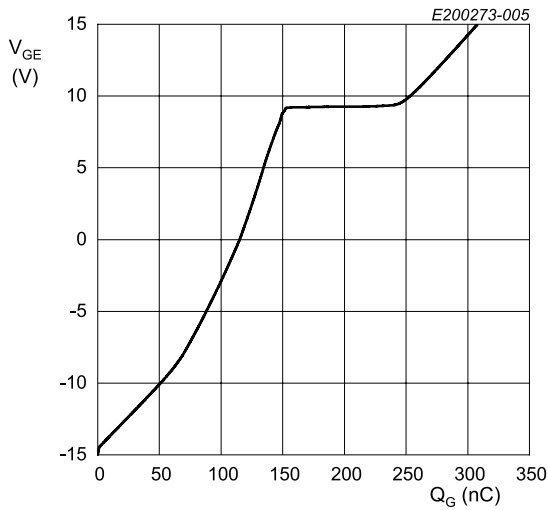


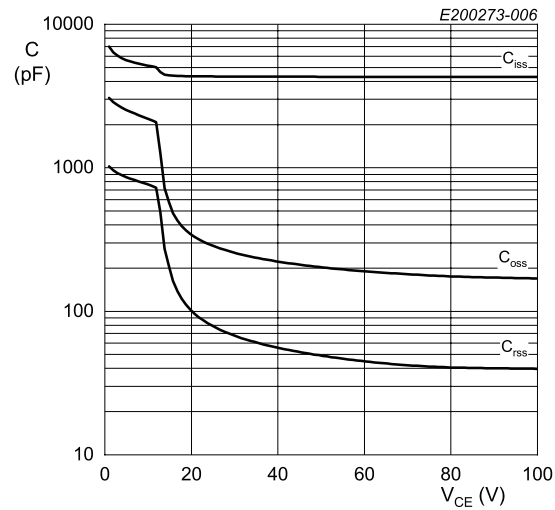
Fig. 4. Diode typical forward characteristics, D1/D2/D3/D4/D5/D6

Typical Characteristics - IGBT T1/T2/T3/T4 and Diode D1/D2/D3/D4/D5/D6



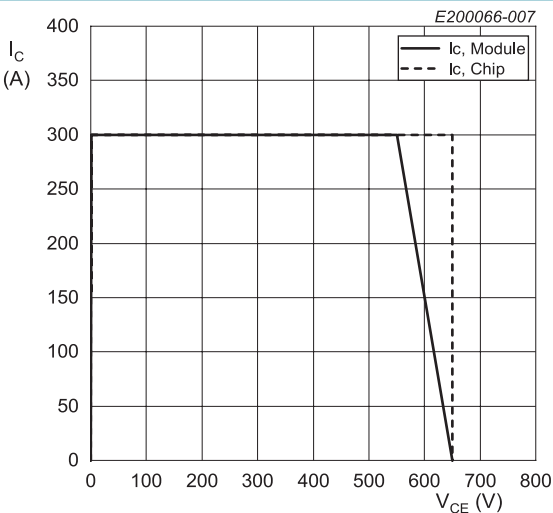
$I_C = 100\text{ A}$; $V_{CC} = 300\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$

Fig. 5. Typical gate charge, T1/T2/T3/T4



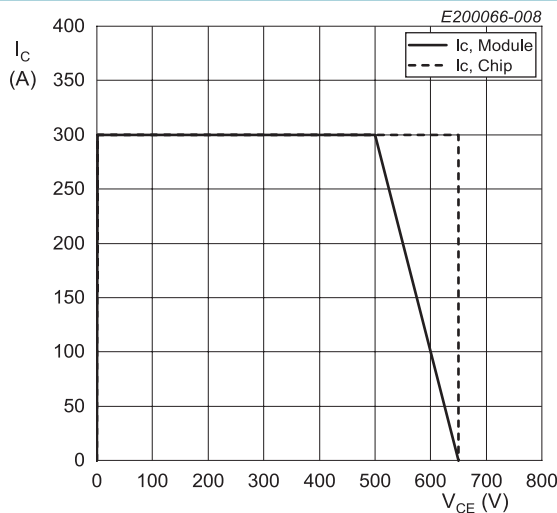
$V_{GE} = 0$; $f = 1\text{ MHz}$; $T_J = 25\text{ }^\circ\text{C}$

Fig. 6. Typical capacitance as a function of collector emitter voltage, T1/T2/T3/T4



$R_g = 10\text{ }\Omega$; $V_{GE} = \pm 15\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$

Fig. 7. Reverse bias safe operating area, T1/T4



$R_g = 10\text{ }\Omega$; $V_{GE} = \pm 15\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$

Fig. 8. Reverse bias safe operating area, T2/T3

Typical Characteristics - IGBT T1/T2/T3/T4 and Diode D1/D2/D3/D4/D5/D6

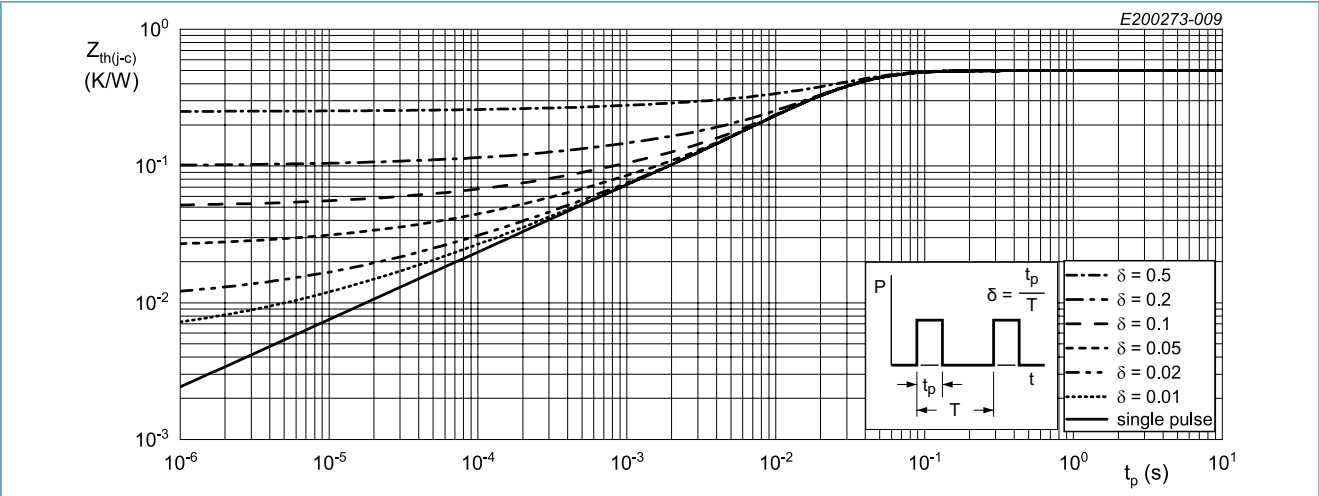


Fig. 9. Typical Transient thermal impedance IGBT, T1/T2/T3/T4

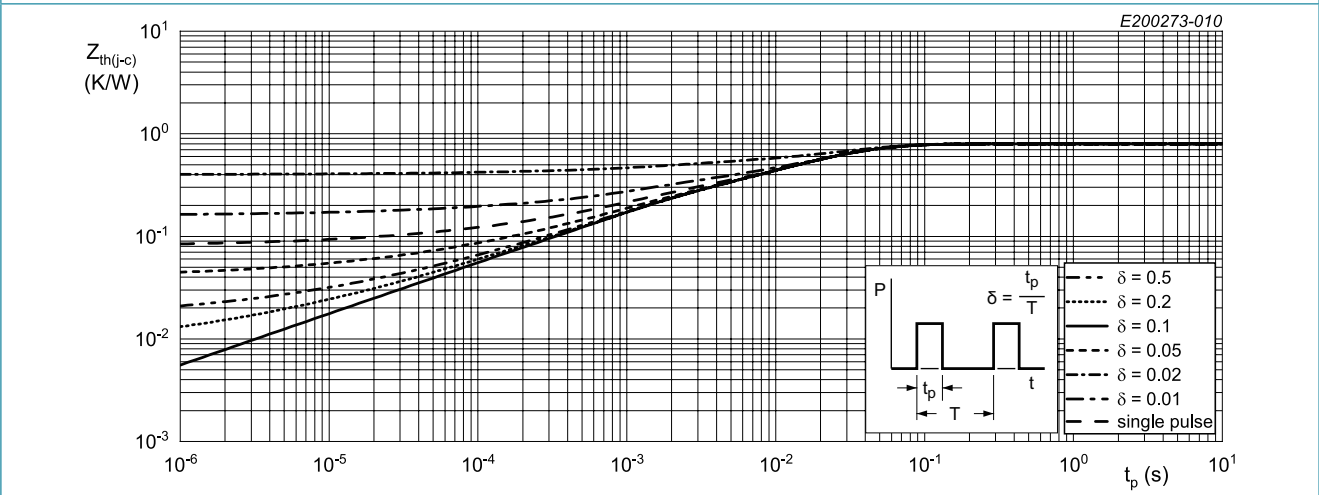
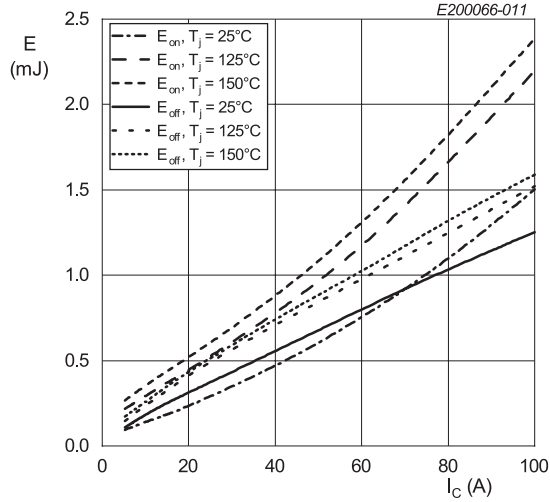


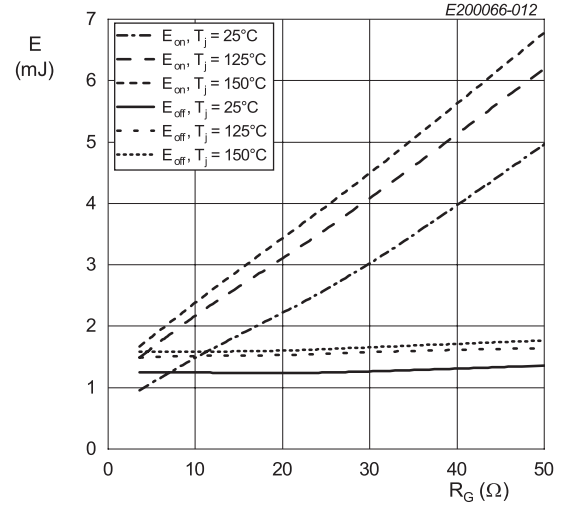
Fig. 10. Typical Transient thermal impedance Diode, D1/D2/D3/D4/D5/D6

Typical Characteristics - IGBT T1/T4 Comutates Diode D5/D6



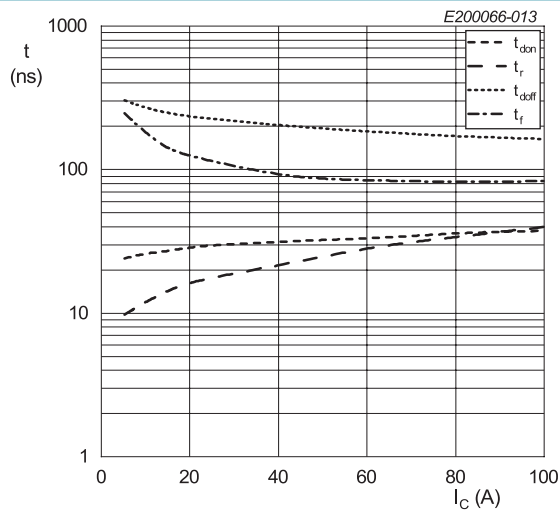
$R_g = 10 \Omega$; $V_{GE} = \pm 15V$;
 $V_{CE} = 300 V$; inductive load

Fig. 11. Typical switching energy loss as a function of collector current, T1/T4



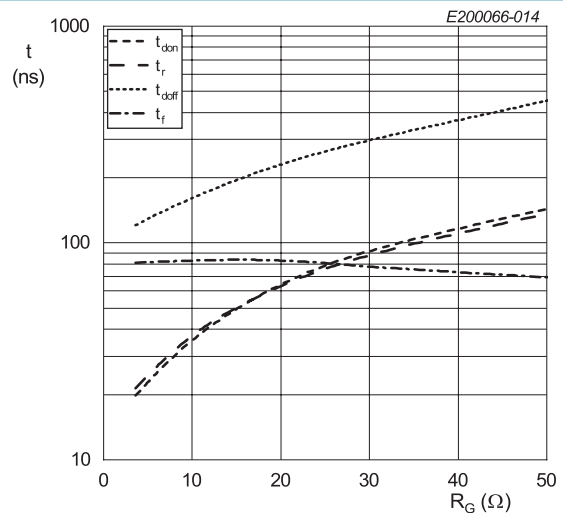
$I_C = 100 A$; $V_{GE} = \pm 15V$;
 $V_{CE} = 300 V$; inductive load

Fig. 12. Typical switching energy loss as a function of gate resistance, T1/T4



$R_g = 10 \Omega$; $V_{GE} = \pm 15V$; $T_j = 150 ^\circ C$;
 $V_{CE} = 300 V$; inductive load

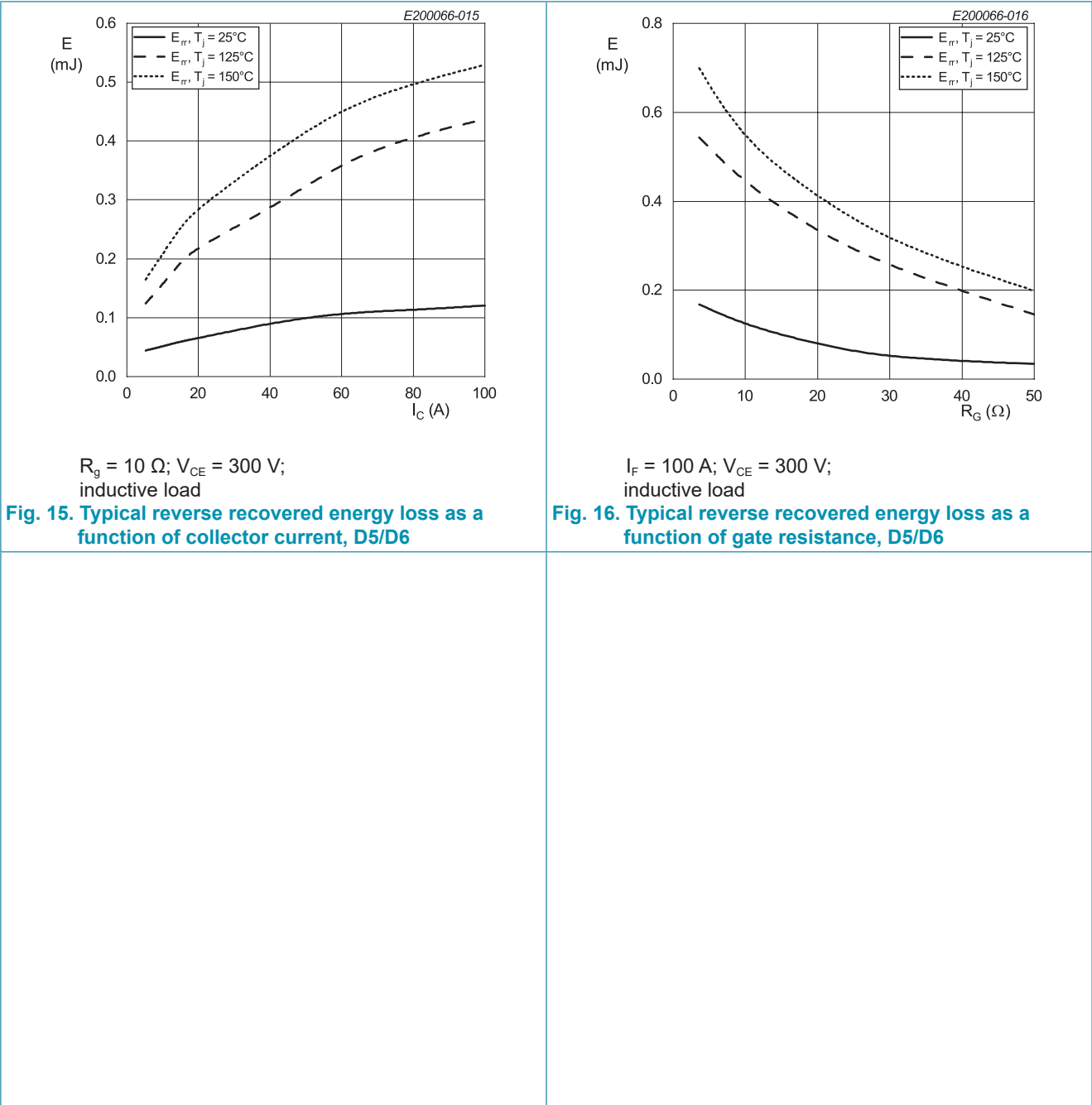
Fig. 13. Typical switching times as a function of collector current, T1/T4



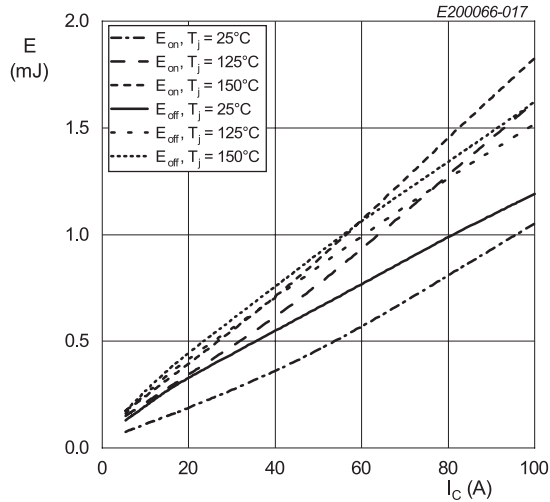
$I_C = 100 A$; $V_{GE} = \pm 15V$; $T_j = 150 ^\circ C$;
 $V_{CE} = 300 V$; inductive load

Fig. 14. Typical switching times as a function of gate resistance, T1/T4

Typical Characteristics - IGBT T1/T4 Comutates Diode D5/D6

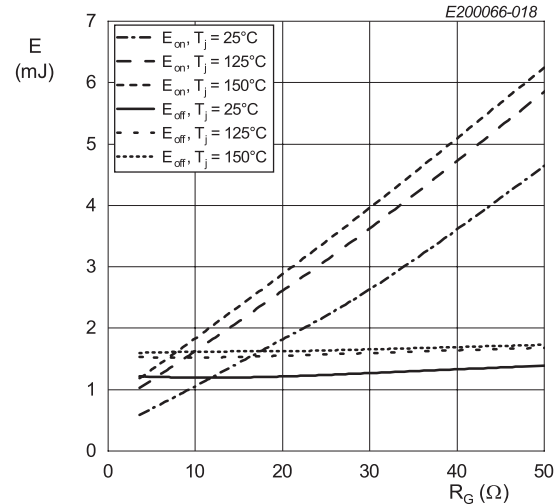


Typical Characteristics - IGBT T2/T3 Comutates Diode D1/D4



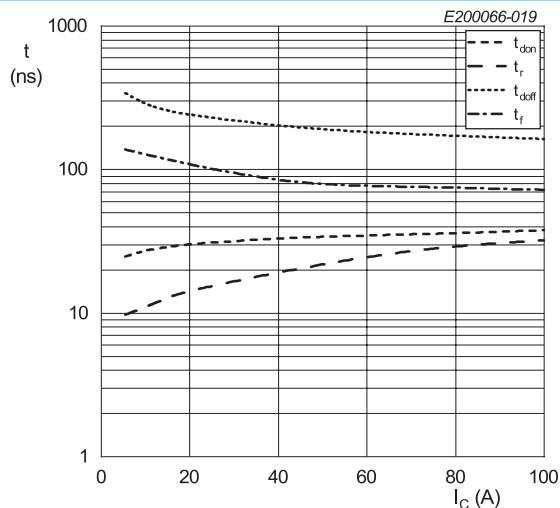
$R_g = 10 \Omega$; $V_{GE} = \pm 15V$;
 $V_{CE} = 300 V$; inductive load

Fig. 17. Typical switching energy loss as a function of collector current, T2/T3



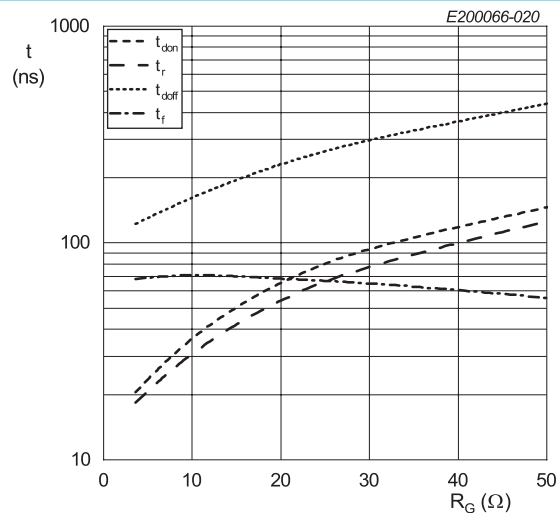
$I_C = 100 A$; $V_{GE} = \pm 15V$;
 $V_{CE} = 300 V$; inductive load

Fig. 18. Typical switching energy loss as a function of gate resistance, T2/T3



$R_g = 10 \Omega$; $V_{GE} = \pm 15V$; $T_j = 150 ^\circ C$;
 $V_{CE} = 300 V$; inductive load

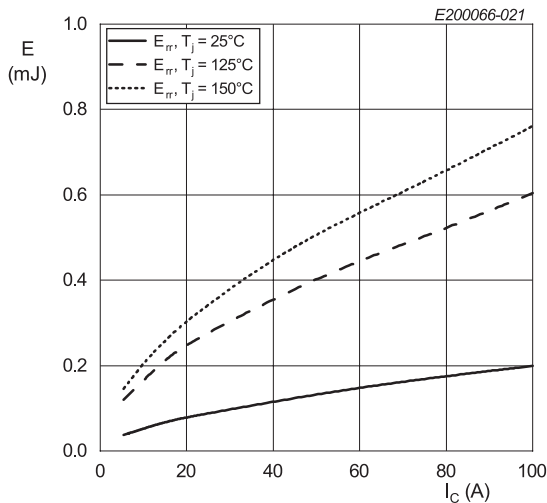
Fig. 19. Typical switching times as a function of collector current, T2/T3



$I_C = 100 A$; $V_{GE} = \pm 15V$; $T_j = 150 ^\circ C$;
 $V_{CE} = 300 V$; inductive load

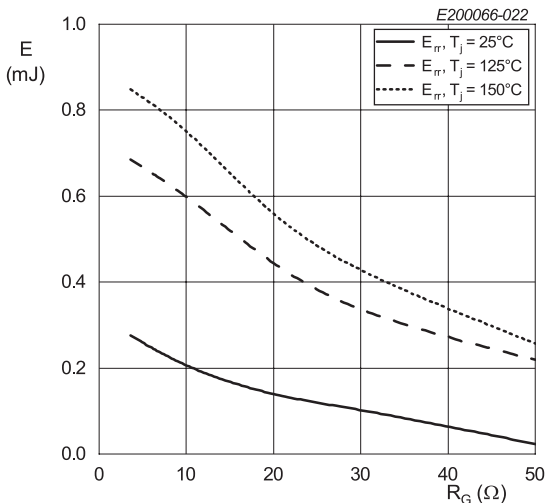
Fig. 20. Typical switching times as a function of gate resistance, T2/T3

Typical Characteristics - IGBT T2/T3 Comutates Diode D1/D4



$R_g = 10\ \Omega$; $V_{CE} = 300\ \text{V}$;
inductive load

Fig. 21. Typical reverse recovered energy loss as a function of collector current, D1/D4



$I_F = 100\ \text{A}$; $V_{CE} = 300\ \text{V}$;
inductive load

Fig. 22. Typical reverse recovered energy loss as a function of gate resistance, D1/D4

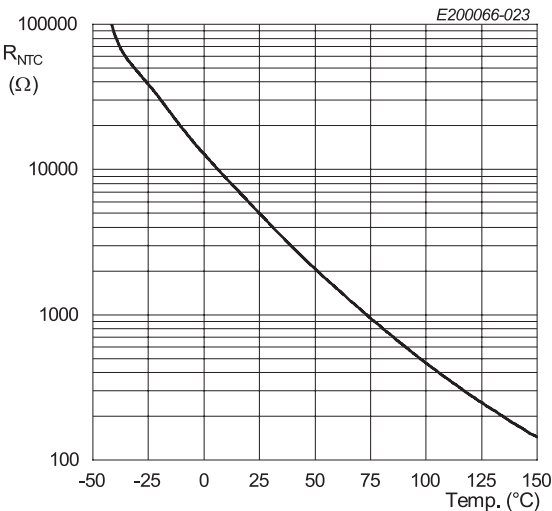
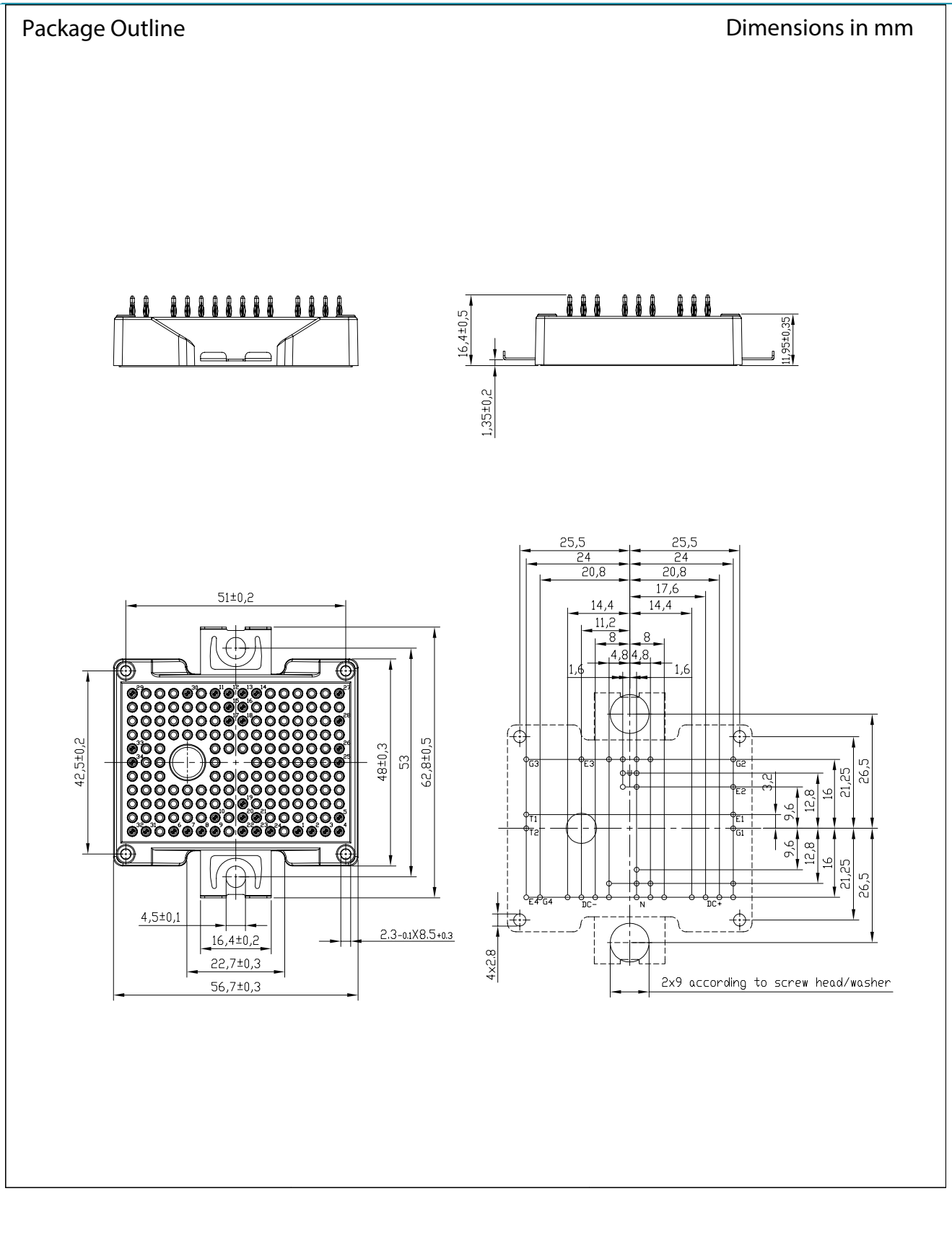


Fig. 23. Typical NTC characteristic as a function of temperature

10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.ween-semi.com>.

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